

## 2SK3446

### Silicon N Channel Power MOS FET Power Switching

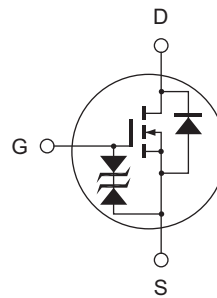
REJ03G1100-0800  
(Previous: ADE-208-1566F)  
Rev.8.00  
Sep 07, 2005

#### Features

- Capable of 2.5 V gate drive
- Low drive current
- Low on-resistance  
 $R_{DS(on)} = 1.5 \Omega$  typ. (at  $V_{GS} = 4 V$ )

#### Outline

RENESAS Package code: PRSS0003DC-A  
(Package name: TO-92MOD)



1. Source
2. Drain
3. Gate

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V <sub>DSS</sub>	150	V
Gate to source voltage	V <sub>GSS</sub>	±10	V
Drain current	I <sub>D</sub>	1	A
Drain peak current	I <sub>D (pulse)</sub> <sup>Note 1</sup>	4	A
Body-drain diode reverse drain current	I <sub>DR</sub>	1	A
Channel dissipation	P <sub>ch</sub> <sup>Note 2</sup>	0.9	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%  
2. Value at Ta = 25°C

## Electrical Characteristics

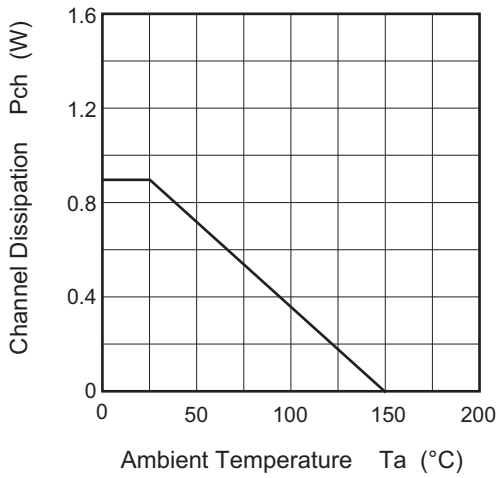
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	150	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±10	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±8 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS (off)</sub>	0.5	—	1.5	V	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA
Static drain to source on state resistance	R <sub>DS (on)</sub>	—	1.5	1.95	Ω	I <sub>D</sub> = 0.5 A, V <sub>GS</sub> = 4 V <sup>Note 3</sup>
	R <sub>DS (on)</sub>	—	1.9	2.5	Ω	I <sub>D</sub> = 0.5 A, V <sub>GS</sub> = 2.5 V <sup>Note 3</sup>
Forward transfer admittance	y <sub>fs</sub>	0.8	1.4	—	S	I <sub>D</sub> = 0.5 A, V <sub>DS</sub> = 10 V <sup>Note 3</sup>
Input capacitance	C <sub>iss</sub>	—	98	—	pF	V <sub>DS</sub> = 10 V V <sub>GS</sub> = 0 f = 1 MHz
Output capacitance	C <sub>oss</sub>	—	31	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	14	—	pF	
Total gate charge	Q <sub>g</sub>	—	3.5	—	nC	V <sub>DD</sub> = 100 V
Gate to source charge	Q <sub>gs</sub>	—	0.5	—	nC	V <sub>GS</sub> = 4 V
Gate to drain charge	Q <sub>gd</sub>	—	1.8	—	nC	I <sub>D</sub> = 1 A
Turn-on delay time	t <sub>d (on)</sub>	—	8	—	ns	V <sub>GS</sub> = 4 V
Rise time	t <sub>r</sub>	—	12	—	ns	I <sub>D</sub> = 0.5 A
Turn-off delay time	t <sub>d (off)</sub>	—	34	—	ns	R <sub>L</sub> = 60 Ω
Fall time	t <sub>f</sub>	—	19	—	ns	
Body-drain diode forward voltage	V <sub>DF</sub>	—	1.0	1.5	V	I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0
Body-drain diode reverse recovery time	t <sub>rr</sub>	—	60	—	ns	I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 di <sub>F</sub> /dt = 100 A/μs

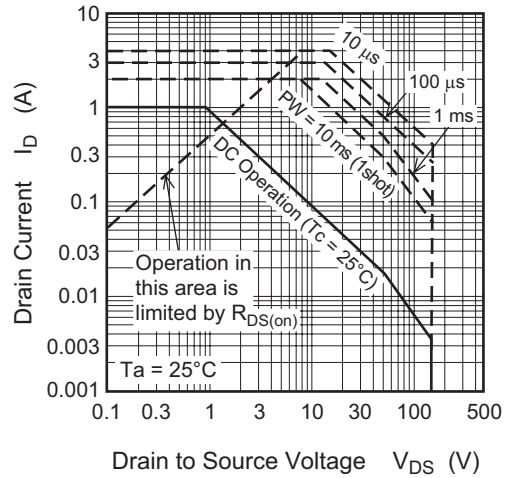
Note: 3. Pulse test

主要特性 (Main Characteristics)

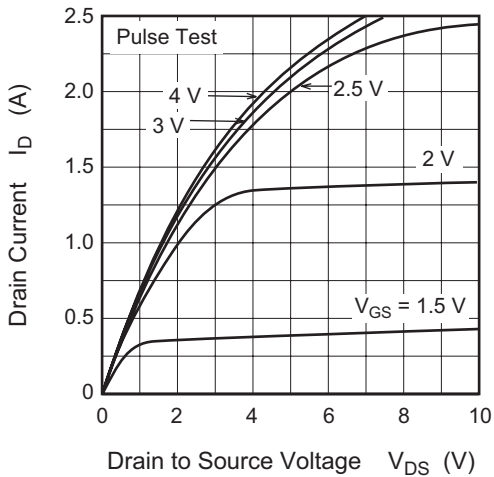
Power vs. Temperature Derating



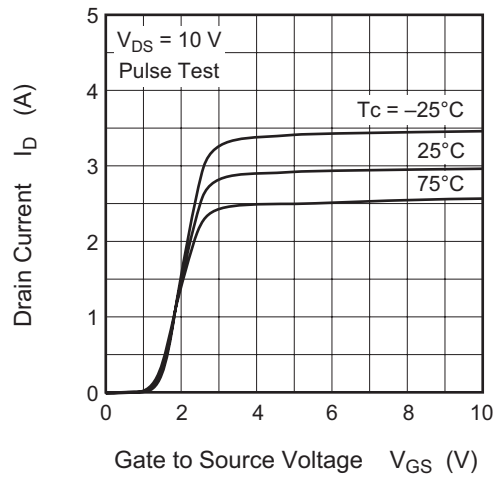
Maximum Safe Operation Area



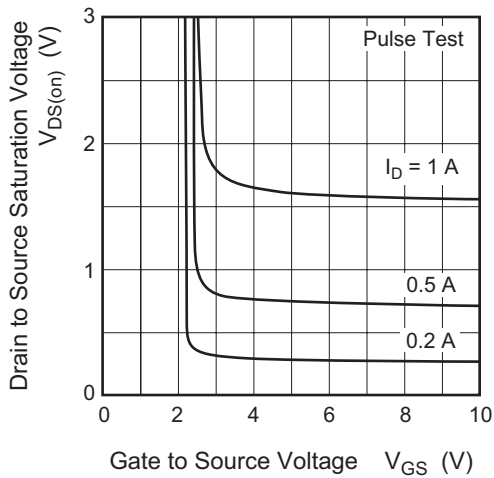
Typical Output Characteristics



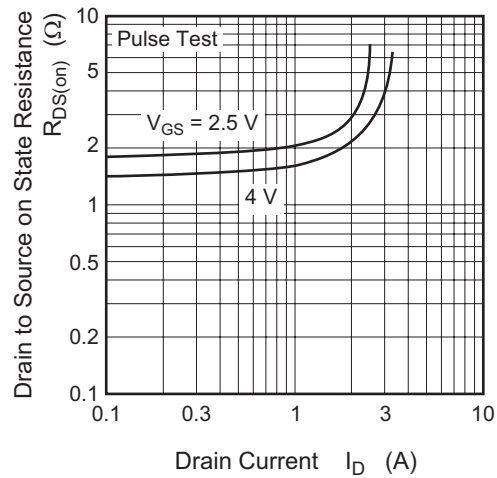
Typical Transfer Characteristics



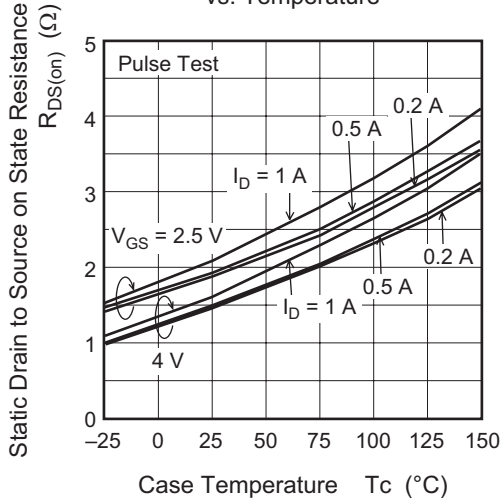
Drain to Source Saturation Voltage vs. Gate to Source Voltage



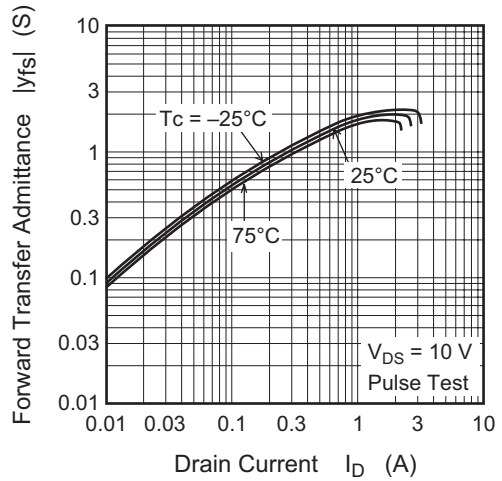
Static Drain to Source on State Resistance vs. Drain Current



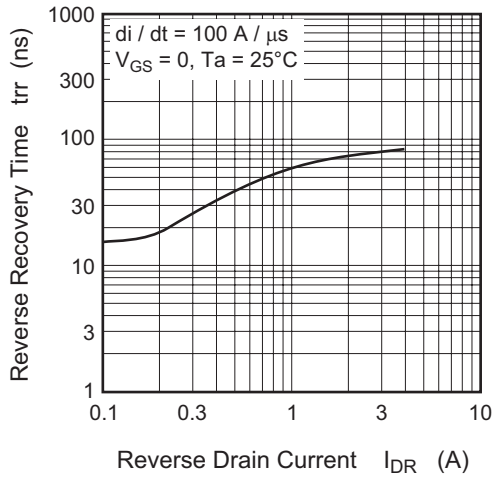
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 Drain to Source on State Resistance vs. Temperature



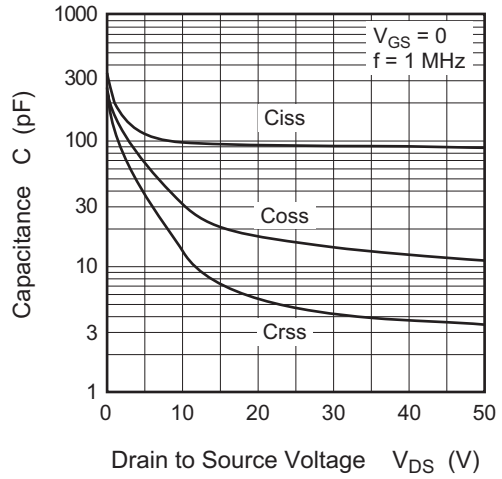
Forward Transfer Admittance vs. Drain Current



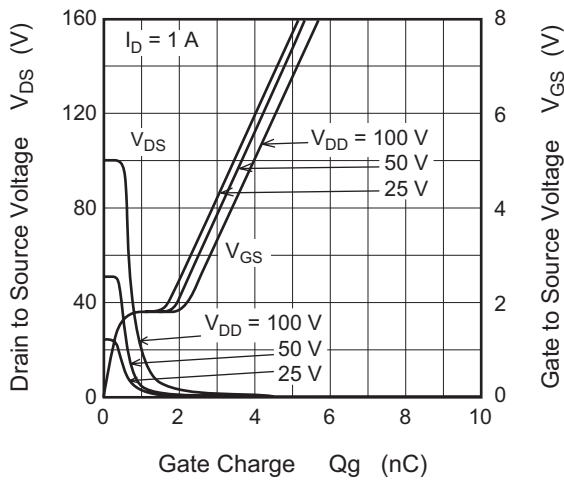
Body-Drain Diode Reverse Recovery Time



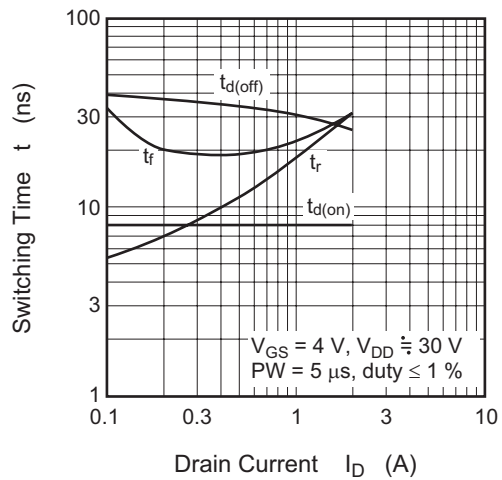
Typical Capacitance vs. Drain to Source Voltage



Dynamic Input Characteristics

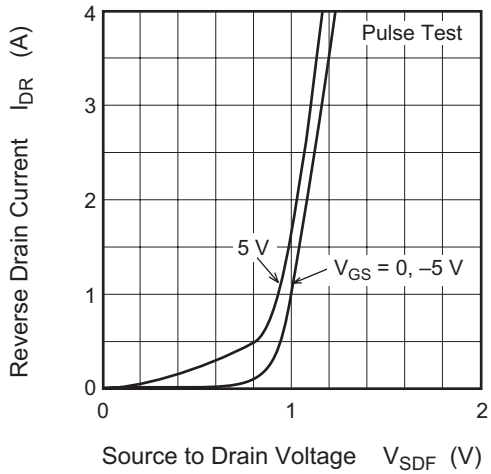


Switching Characteristics

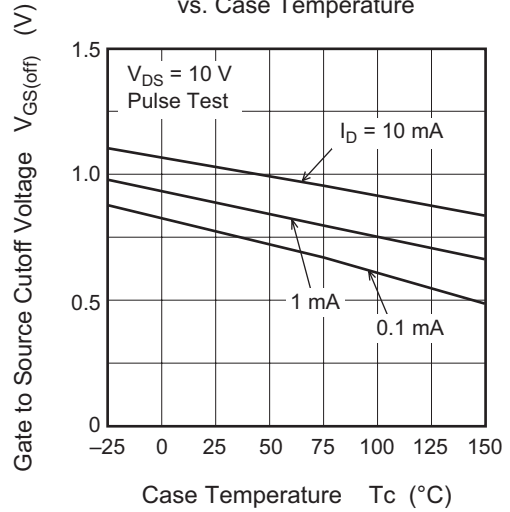


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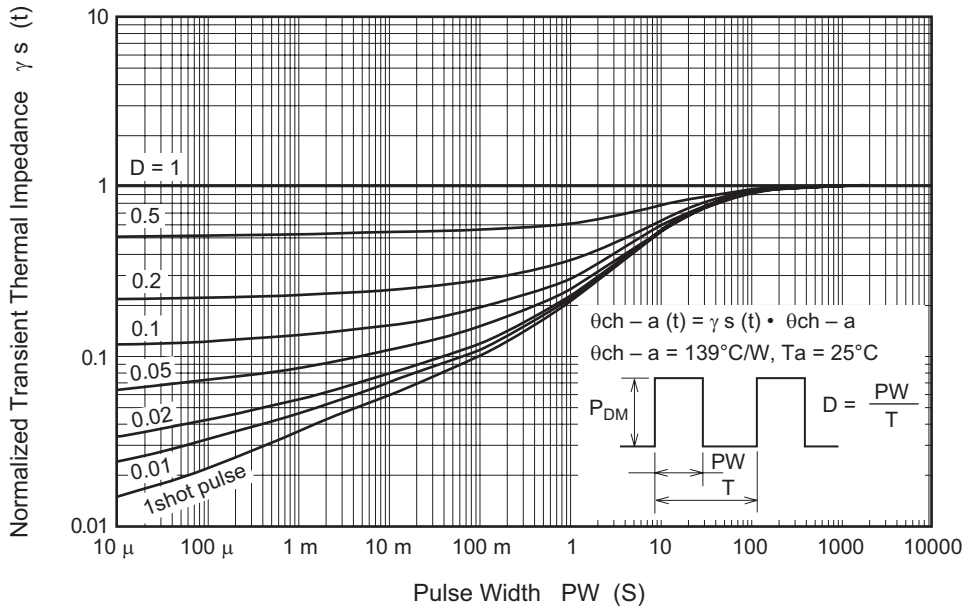
Reverse Drain Current vs. Source to Drain Voltage



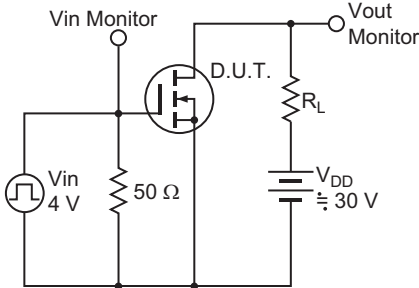
Gate to Source Cutoff Voltage vs. Case Temperature



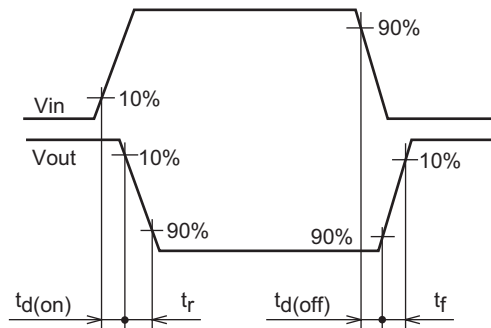
Normalized Transient Thermal Impedance vs. Pulse Width



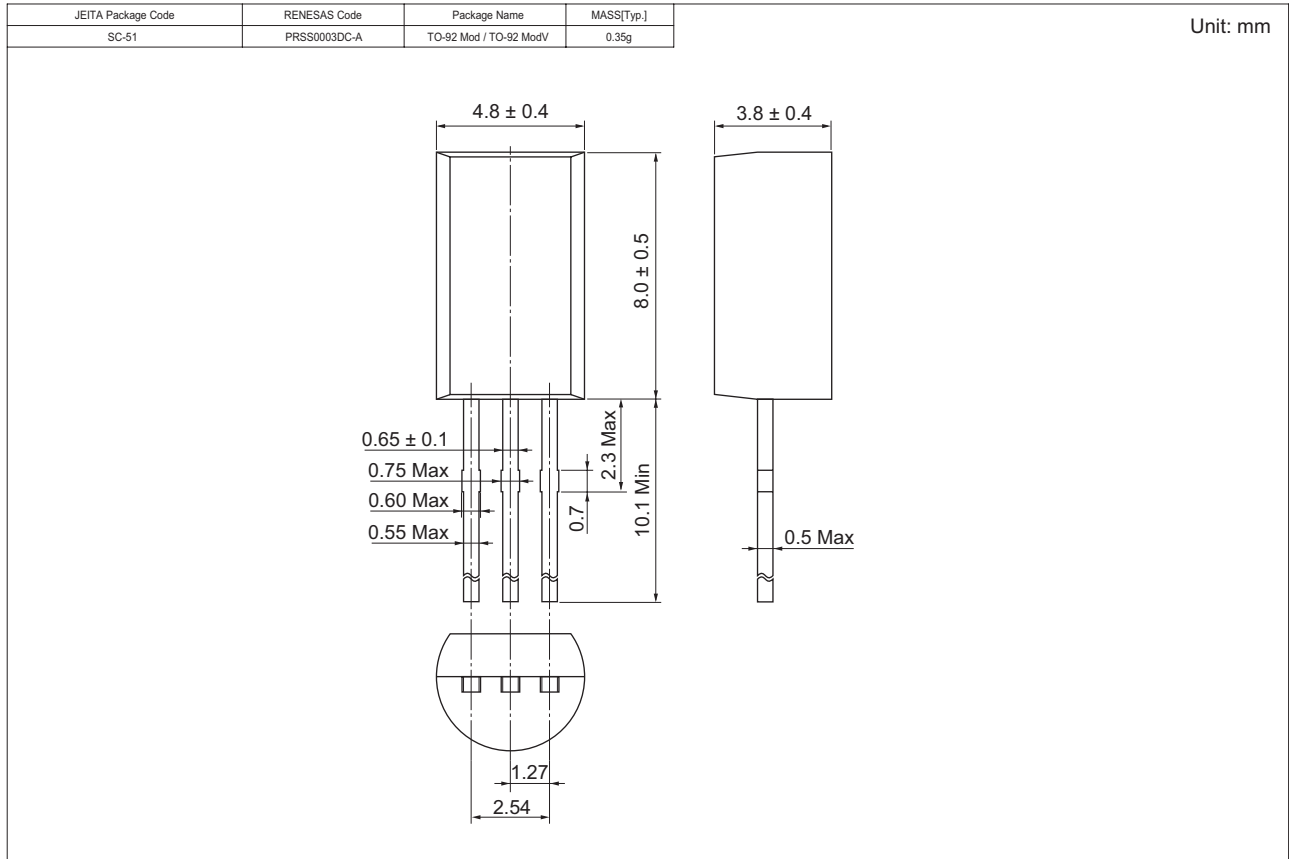
Switching Time Test Circuit



Waveform



Package Dimensions 供应商



Ordering Information

Part Name	Quantity	Shipping Container
2SK3446TZ-E	2500 pcs	Hold box, Radial taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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